WHAT IS CLAIMED IS:

1. A TFT LCD device, comprising:

a substrate;

a thin film transistor formed on said substrate, having a source electrode and a drain electrode;

an insulating layer formed over an entire surface of said substrate on which said thin film transistor is formed, having a contact hole exposing a portion of the drain electrode; and

a pixel electrode corresponding to the thin film transistor, formed on said insulating layer and connected to the drain electrode through the contact hole,

wherein said pixel electrode is formed of a multi-layered conductive layer.

2. The TFT LCD device according to claim 1, wherein the drain electrode is composed of multiple layers, and an uppermost layer of the multiple layers is one selected from a Cr layer and a MoW layer.

3. The TFT LCD device according to claim 2, wherein the multi-layered conductive layer is composed of two-layered conductive layer having a lower layer of same material as the uppermost layer of the multiple layers, and an upper layer of Al-containing metal.

4. The TFT LCD device according to claim 2, wherein the multi-layered

conductive layer is composed of a three-layered conductive layer having a lower layer of same material as the uppermost layer of the multiple layers, an upper layer of Al-containing metal, and an intermediate layer of material having a electro-negativity that is in a middle level of the lower layer and the upper layer.

5. The TFT LCD device according to claim 2, wherein the multiple layers are composed of a three-layered layer including a lower MoW layer and an intermediate Al-containing metal layer.

6. The TFT LCD device according to claim 1, wherein said thin film transistor is a top gate type polysilicon thin film transistor.

7. The TFT LCD device according to claim 1, wherein said insulating layer is composed of a photo-sensitive organic insulating layer.

8. The TFT LCD device according to claim 2, wherein small projections that work as micro lens are formed on an upper surface of said insulating layer.